

## ABSTRACT OF THE DISCLOSURE

A nitride semiconductor laser device includes a nitride semiconductor substrate, and a layered portion corresponding to a nitride semiconductor film grown on the nitride semiconductor substrate, the  
5 layered portion including an n-type layer and a p-type layer and a light emitting layer posed between the n- and p-type layers, of the n- and p-type layers a layer opposite to the nitride semiconductor substrate with the light emitting layer opposed therebetween serving as an upper layer having a stripe of 1.9  $\mu\text{m}$  to 3.0  $\mu\text{m}$  in width, the light emitting layer and the upper  
10 layer having an interface distant from a bottom of the stripe by 0  $\mu\text{m}$  to 0.2  $\mu\text{m}$ .